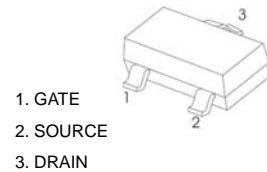


3415

P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-12V	45mΩ@-4.5V	-4.1A
	60mΩ@-2.5V	
	90mΩ@-1.8V	

SOT-23



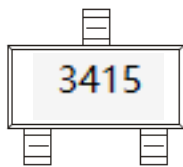
FEATURE

- TrenchFET Power MOSFET

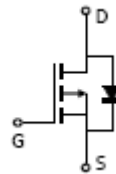
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±8	
Continuous Drain Current	I_D	-4.1	A
Continuous Source-Drain Diode Current	I_S	-0.8	
Maximum Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient($t \leq 10s$)	$R_{\theta JA}$	357	$^{\circ}C/W$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-50 ~ +150	$^{\circ}C$

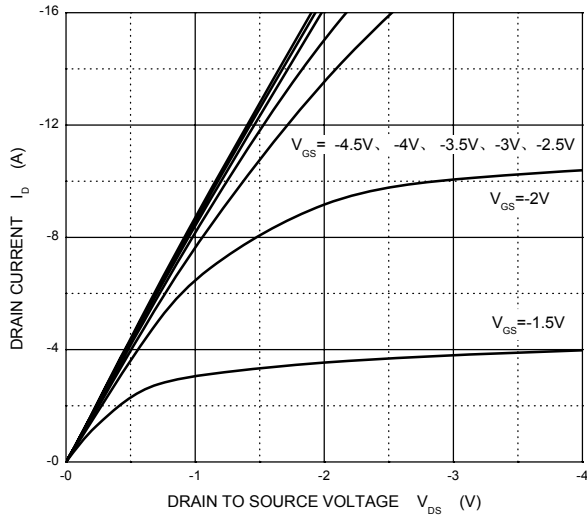
$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.5		-0.9	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -8V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance ^e	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -3.5A$		30	45	m Ω
		$V_{GS} = -2.5V, I_D = -3A$		40	60	
		$V_{GS} = -1.8V, I_D = -2.0A$		60	90	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -4.1A$	6			S
Dynamic						
Input capacitance ^{b,c}	C_{iss}	$V_{DS} = -4V, V_{GS} = 0V, f = 1MHz$		740		pF
Output capacitance ^{b,c}	C_{oss}			290		
Reverse transfer capacitance ^{b,c}	C_{rss}			190		
Total gate charge ^b	Q_g	$V_{DS} = -4V, V_{GS} = -4.5V, I_D = -4.1A$		7.8	15	nC
		$V_{DS} = -4V, V_{GS} = -2.5V, I_D = -4.1A$		4.5	9	
Gate-source charge ^b	Q_{gs}	$V_{DS} = -4V, V_{GS} = -2.5V, I_D = -4.1A$		1.2		
Gate-drain charge ^b	Q_{gd}			1.6		
Gate resistance ^{b,c}	R_g	$f = 1MHz$	1.4	7	14	Ω
Turn-on delay time ^{b,c}	$t_{d(on)}$	$V_{DD} = -4V, R_L = 1.2\Omega, I_D \approx -3.3A, V_{GEN} = -4.5V, R_g = 1\Omega$		13	20	ns
Rise time ^{b,c}	t_r			35	53	
Turn-off Delay time ^{b,c}	$t_{d(off)}$			32	48	
Fall time ^{b,c}	t_f			10	20	
Turn-on delay time ^{b,c}	$t_{d(on)}$	$V_{DD} = -4V, R_L = 1.2\Omega, I_D \approx -3.3A, V_{GEN} = -8V, R_g = 1\Omega$		5	10	ns
Rise time ^{b,c}	t_r			11	17	
Turn-off delay time ^{b,c}	$t_{d(off)}$			22	33	
Fall time ^{b,c}	t_f			16	24	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ C$			-1.4	A
Pulse diode forward current ^a	I_{SM}				-10	
Body diode voltage	V_{SD}	$I_F = -3.3A$			-1.2	V

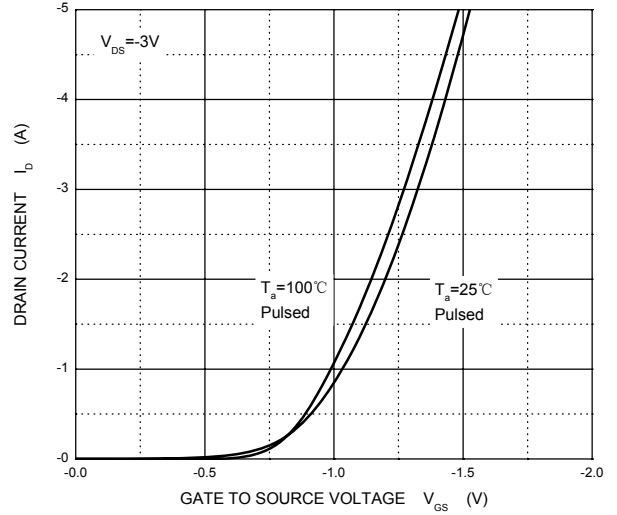
Note :

- a. Pulse Test ; Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. These parameters have no way to verify.

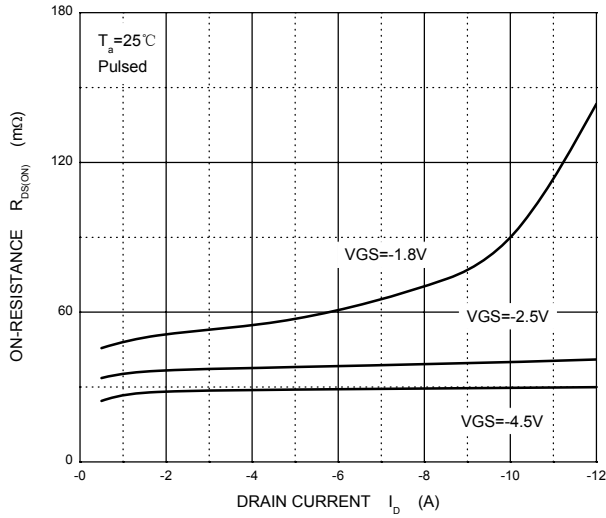
Output Characteristics



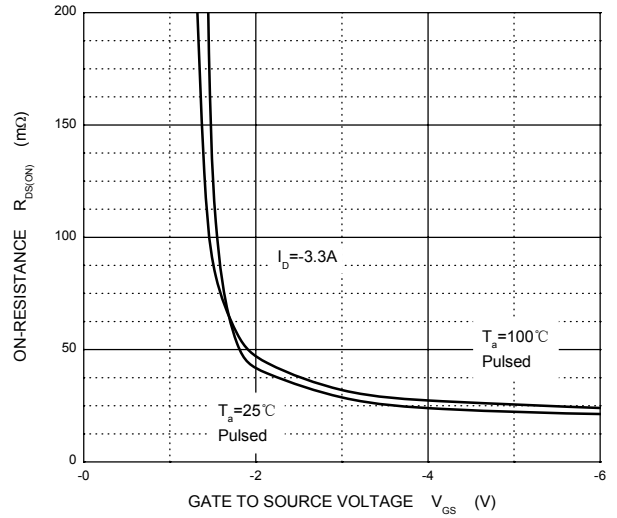
Transfer Characteristics



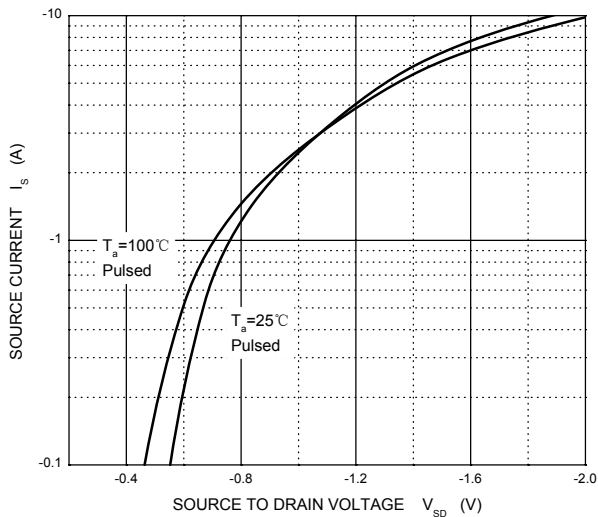
$R_{DS(ON)}$ — I_D



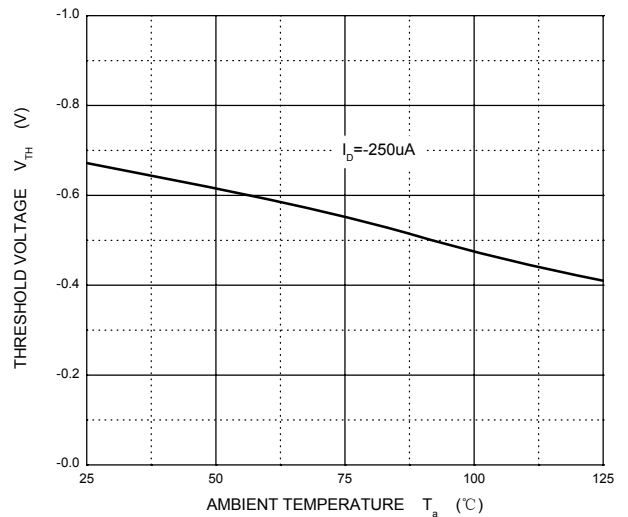
$R_{DS(ON)}$ — V_{GS}

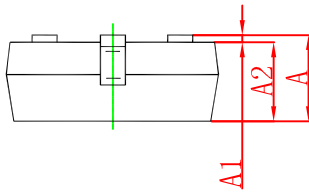
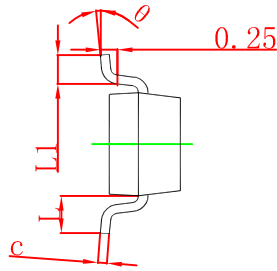
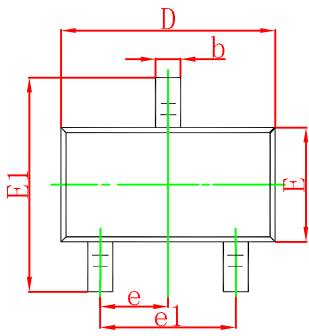


I_S — V_{SD}

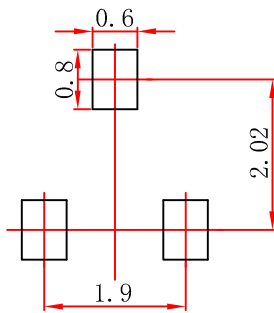


Threshold Voltage



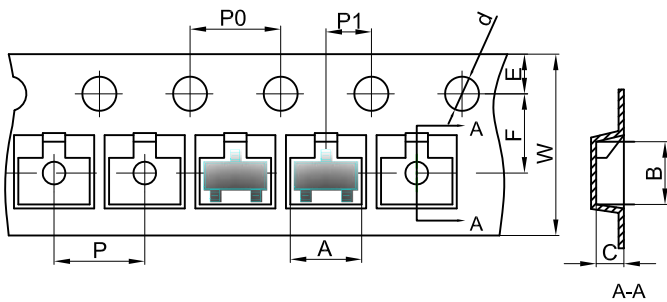


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°



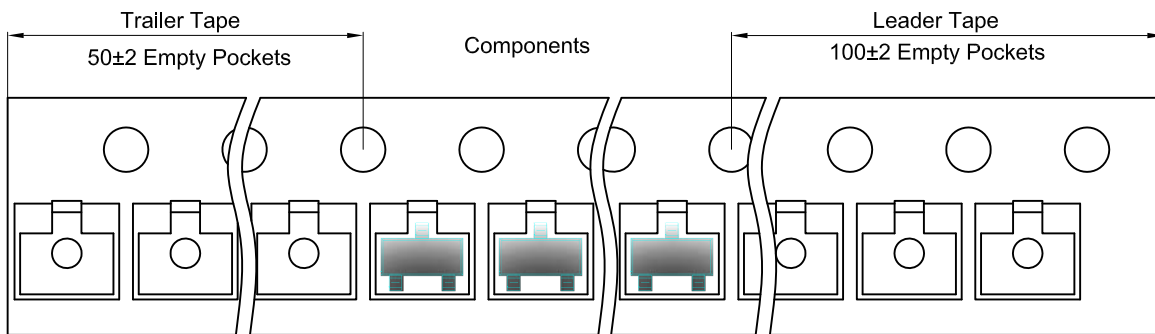
Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

SOT-23

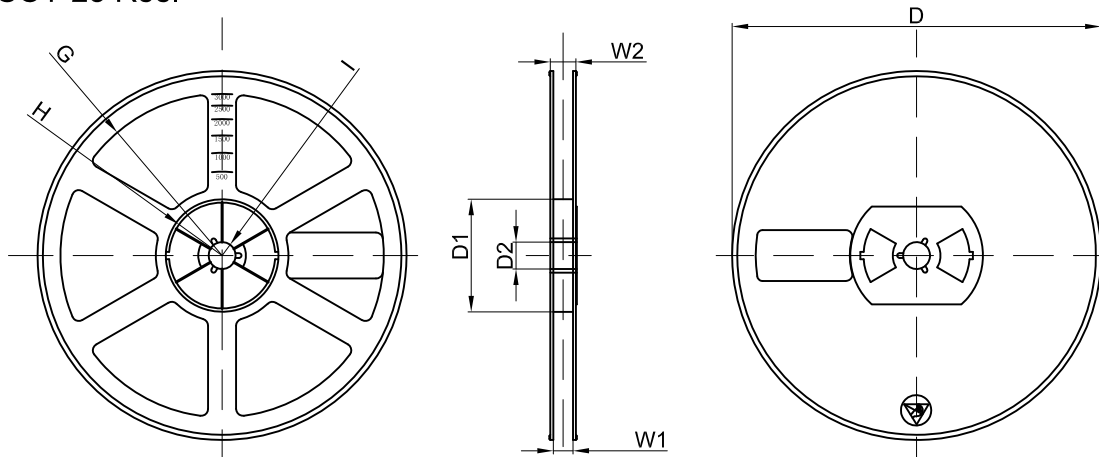


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size
3000 pcs	7 inch